

Silicon PNP Power Transistors

2SA1887

DESCRIPTION

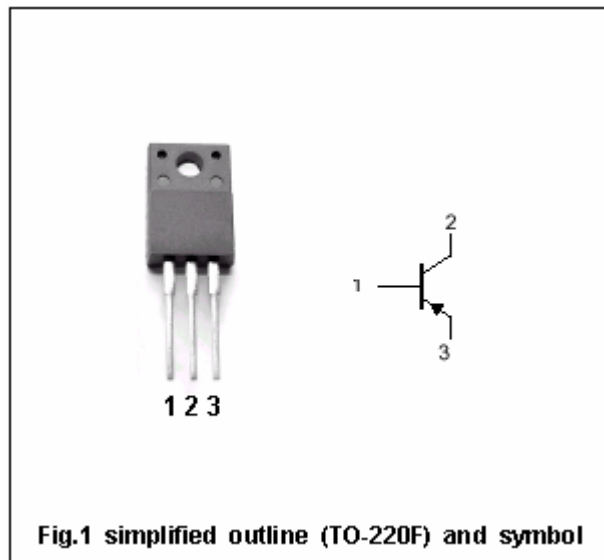
- With TO-220F package
- Low collector saturation voltage

APPLICATIONS

- High current switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-80	V
V _{CEO}	Collector-emitter voltage	Open base	-50	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-10	A
P _C	Collector dissipation	T _C =25°C	25	W
		T _a =25°C	2.0	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-10mA ; I_B=0$	-50			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-5A ; I_B=-0.25A$		-0.2	-0.4	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-5A ; I_B=-0.25A$		-0.95	-1.4	V
I_{CBO}	Collector cut-off current	$V_{CB}=-70V ; I_E=0$			-1.0	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-7V ; I_C=0$			-1.0	μA
h_{FE}	DC current gain	$I_C=-1A ; V_{CE}=-1V$	120		400	
C_{OB}	Output capacitance	$I_E=0 ; V_{CB}=-10V ; f=1MHz$		215		pF
f_T	Transition frequency	$I_C=-1A ; V_{CE}=-1V$		45		MHz

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PACKAGE OUTLINE

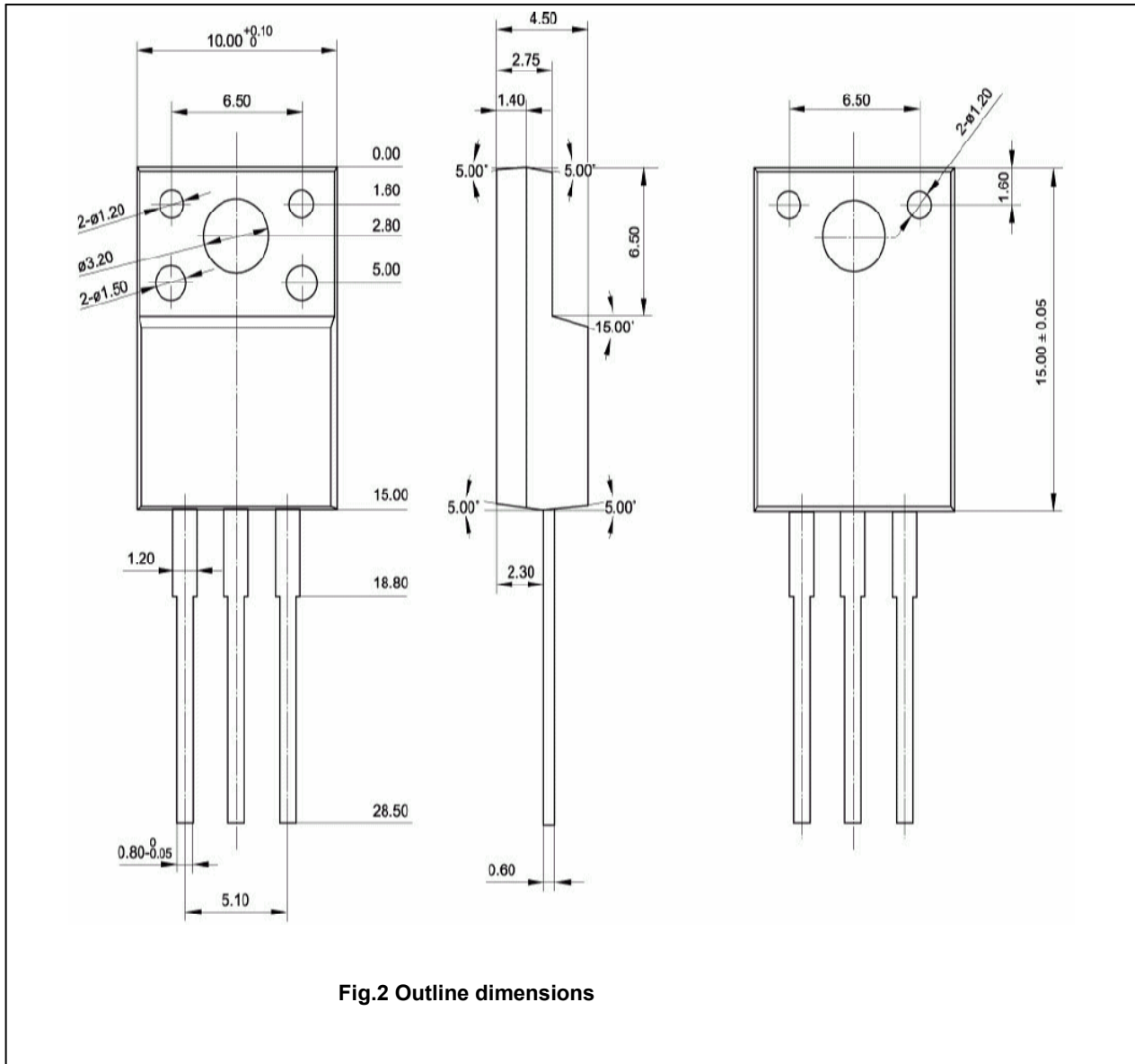


Fig.2 Outline dimensions